

Product Overview

NSS20501UW3: Low VCE(sat) Transistor, NPN, 20 V, 5.0 A

For complete documentation, see the data sheet.

Low VCE(sat) Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage VCE(sat) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Features

- High Current, Low VCE(sat), ESD Robust, High Current Gain, High Cut Off Frequency, Low Profile Package, Linear Gain (Beta)

Benefits

- Improved Circuit Efficiency, Decreased Battery Charge Time, Reduce component count, High Frequency Switching, Smaller Portable Product, No distortion

Applications

- Load Switching, Battery Charging, External Pass Transistor, DC/DC Converter, Complimentary Driver, Current Extention & Low Drop Out Regulation, Cathode Florescent Lamp drive, Peripheral Driver - LEDs, Motors, Relays

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Polarity	Type	V _{CE(sat)} Max (V)	I _C Cont. (A)	V _{CEO} Min (V)	V _{CBO} (V)	V _{EBO} (V)	V _{BE(sat)} (V)	V _{BE(ON)} (V)	h _{FE} Min	h _{FE} Max	f _T Min (MHz)	P _{TM} Max (W)	Package Type
NSS20501UW3T2G	0.1809	Pb-free Halide free non AEC-Q and PPAP	Active	NPN	Low V _{CE(sat)}	0.04	5	20	20	6	0.9	0.9	250	-	150	1.5	WDF N-3
NSS20501UW3TBG	0.1809	Pb-free Halide free non AEC-Q and PPAP	Active	NPN	Low V _{CE(sat)}	0.04	5	20	20	6	0.9	0.9	250	-	150	1.5	WDF N-3

For more information please contact your local sales support at www.onsemi.com.

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